1. General description

Low V_{CEsat} NPN transistor in a SOT883 leadless ultra small plastic package.

PNP complement: PBSS3540M.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency leading to reduced heat generation
- · Reduced printed-circuit board requirements.
- AEC-Q101 qualified

3. Applications

- · Power management:
 - DC-DC converter
 - Supply line switching
 - Battery charger
 - LCD backlighting.
- Peripheral driver:
 - Driver in low supply voltage applications (e.g. lamps and LEDs).
 - Inductive load drivers (e.g. relays, buzzers and motors).

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	40	V
I _C	collector current		[1] [2]	-	-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	1	Α
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 10 mA; T _{amb} = 25 °C		200	-	-	
R _{CEsat}	collector-emitter saturation resistance	I_C = 500 mA; I_B = 50 mA; $t_p \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C		-	380	500	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board, (PCB), single-sided copper, tinplated, standard footprint, with 60 μm copper strip line.



^[2] Refer to SOT883 standard mounting conditions.

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	1 🔲	С
2	E	emitter		В
3	С	collector	Transparent top view DFN1006-3 (SOT883)	E sym123

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS2540M	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS2540M	DC

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	40	V
V_{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current		[1] [2]	-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	1	Α
I _{BM}	peak base current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] [2]	-	250	mW
			[2] [3]	-	430	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board, (PCB), single-sided copper, tinplated, standard footprint, with 60 μm copper strip line.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	[1] [2]	-	-	500	K/W
	from junction to ambient		[2] [3] [4]	-	-	290	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint, with 60 µm copper strip line.

^[2] Refer to SOT883 standard mounting conditions.

^[3] Device mounted on an FR4 PCB, single-sided copper, tinplated, mounting pad for collector 1 cm².

^[2] Refer to SOT883 standard mounting conditions.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

^[4] Operated under pulsed conditions: duty cycle $\delta \le 20\%$, pulse width $t_p \le 30$ ms.

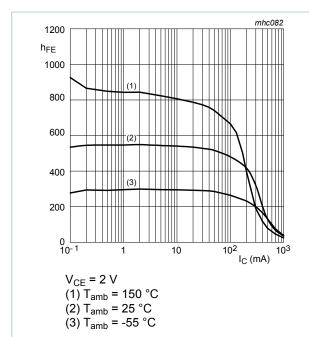
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10. Characteristics

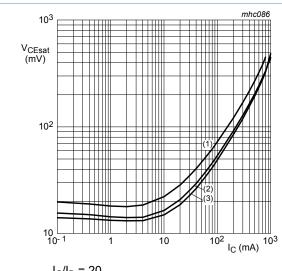
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 10 mA; T _{amb} = 25 °C	200	-	-	
		V_{CE} = 2 V; I_{C} = 100 mA; t_{p} ≤ 300 μs; pulsed; δ ≤ 0.02 ; T_{amb} = 25 °C	150	-	-	
		V_{CE} = 2 V; I_{C} = 500 mA; t_{p} ≤ 300 μs; pulsed; δ ≤ 0.02 ; T_{amb} = 25 °C	50	-	-	
V _{CEsat}	collector-emitter	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C	-	-	50	mV
	saturation voltage	I _C = 100 mA; I _B = 5 mA; T _{amb} = 25 °C	-	-	100	mV
		I_C = 200 mA; I_B = 10 mA; T_{amb} = 25 °C	-	-	200	mV
		I_C = 500 mA; I_B = 50 mA; $t_p \le 300 \mu s$;	-	-	250	mV
R _{CEsat}	collector-emitter saturation resistance	pulsed; δ ≤ 0.02 ; T _{amb} = 25 °C	-	380	500	mΩ
V _{BEsat}	base-emitter saturation voltage		-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 100 mA; T_{amb} = 25 °C	-	-	1.1	V
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	250	450	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; I_{e} = 0 A; I_{e} = 0 A; f = 1 MHz; I_{amb} = 25 °C	-	-	6	pF

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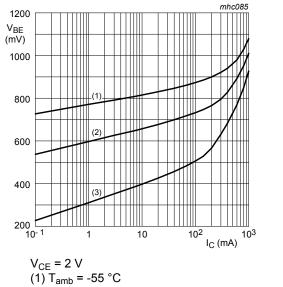


DC current gain as a function of collector Fig. 1. current; typical values



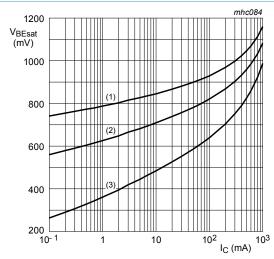
 $I_C/I_B = 20$ (1) $T_{amb} = 150 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}\text{C}$ (3) $T_{amb} = -55 \,^{\circ}\text{C}$

Fig. 3. Collector-emitter saturation voltage as a function of collector current; typical values



(2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = 150 \, ^{\circ}C$

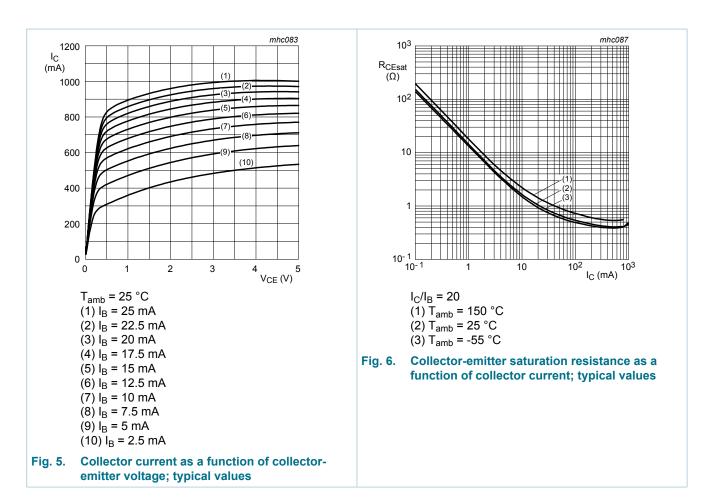
Fig. 2. Base-emitter voltage as a function of collector current; typical values



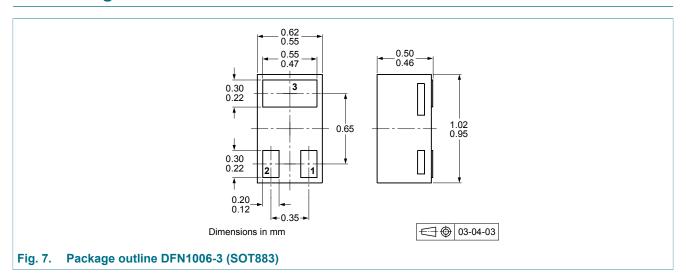
 $I_C/I_B = 20$ (1) $T_{amb} = 150 \,^{\circ}C$ (2) T_{amb} = 25 °C (3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

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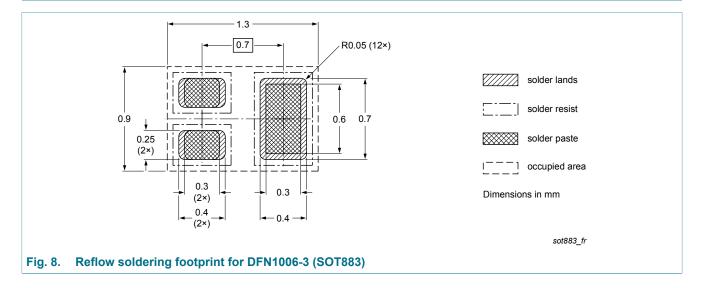


11. Package outline



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12. Soldering



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13. Revision history

Table 8. Revision history

	· y					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS2540M v.2	20180222	Product data sheet	-	PBSS2540M v.1		
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelir of Nexperia. Legal texts have been adapted to the new company name where appropriate. 					
PBSS2540M v.1	20030722	Product data sheet	-	-		

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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